

Characterization and Testbeam Analysis of irradiated Silicon n-in-p Pixel Detectors for the ATLAS Upgrade

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FE-I3 compatible, n-in-p single chip modules, produced in the framework of a joint RD50-ATLAS planar pixel group production have been irradiated up to $5 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$ with protons (KIT and CERN PS) and reactor neutrons (JSI). They were characterized in the laboratory as well as under beam-test conditions at the CERN SPS.

New results on the charge collection performance as well on the high voltage stability will be presented. Additionally, an update on the results from beam-test studies is given.

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